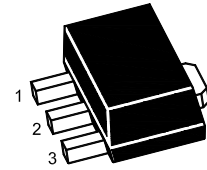


2SD350U

NPN Silicon Epitaxial Planar Power Transistor



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

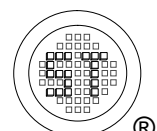
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3	A
Peak Collector Current, Pulsed	I_{CM}	5	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_{tot}	1 ¹⁾ 1.6 ²⁾	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	125 ¹⁾ 78 ²⁾	$^\circ\text{C/W}$

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

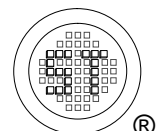
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 0.1\text{ A}$ at $V_{CE} = 2\text{ V}$, $I_C = 0.5\text{ A}$ at $V_{CE} = 2\text{ V}$, $I_C = 1\text{ A}$ at $V_{CE} = 2\text{ V}$, $I_C = 2\text{ A}$ at $V_{CE} = 2\text{ V}$, $I_C = 3\text{ A}$	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	300 300 300 200 100	- - 700 - -	- - - - -
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	50	-	V
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	50	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $I_C = 0.5\text{ A}$, $I_B = 50\text{ mA}$ at $I_C = 1\text{ A}$, $I_B = 50\text{ mA}$ at $I_C = 2\text{ A}$, $I_B = 100\text{ mA}$ at $I_C = 2\text{ A}$, $I_B = 200\text{ mA}$ at $I_C = 3\text{ A}$, $I_B = 300\text{ mA}$	$V_{CE(sat)}$	- - - - -	80 160 280 260 370	mV
Base Emitter Saturation Voltage at $I_C = 2\text{ A}$, $I_B = 100\text{ mA}$ at $I_C = 3\text{ A}$, $I_B = 300\text{ mA}$	$V_{BE(sat)}$	- -	1.1 1.2	V
Base Emitter On Voltage at $V_{CE} = 2\text{ V}$, $I_C = 1\text{ A}$	$V_{BE(ON)}$	-	1.1	V
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	MHz
Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	25	pF



Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

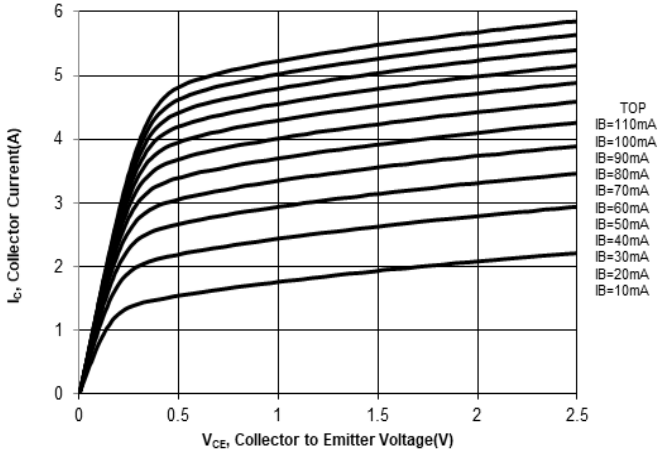


Fig. 2 Collector Current vs. Base to Emitter Voltage

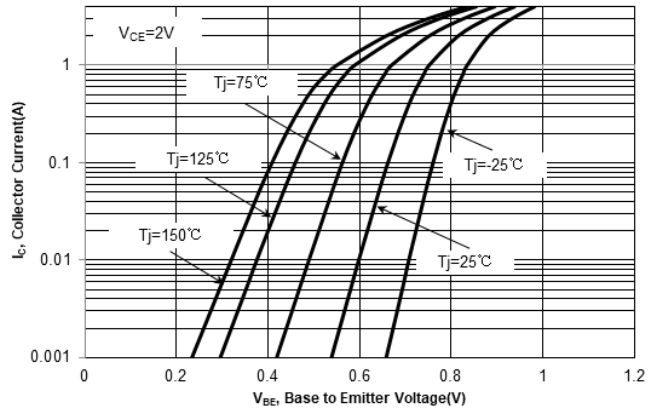


Fig. 3 DC Current Gain vs. Collector Current

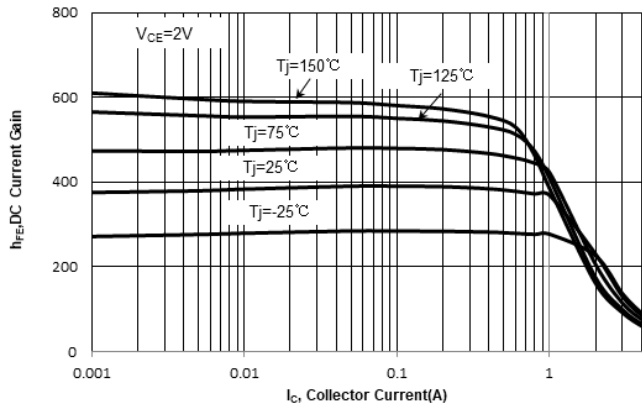
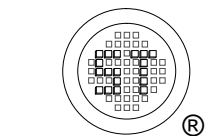
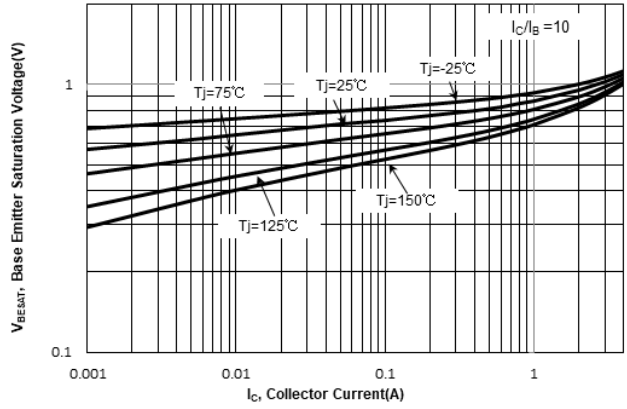


Fig. 4 V_{BESAT} vs. Collector Current



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Electrical Characteristics Curves

Fig. 5 V_{CESAT} vs. Collector Current

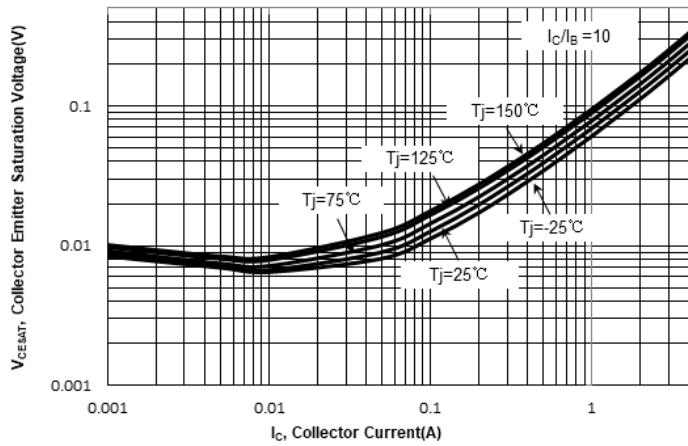


Fig. 6 Output Capacitance

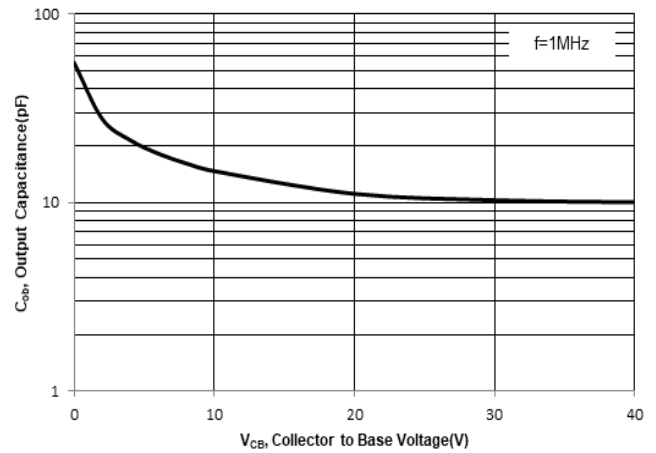
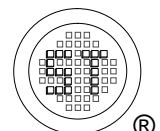
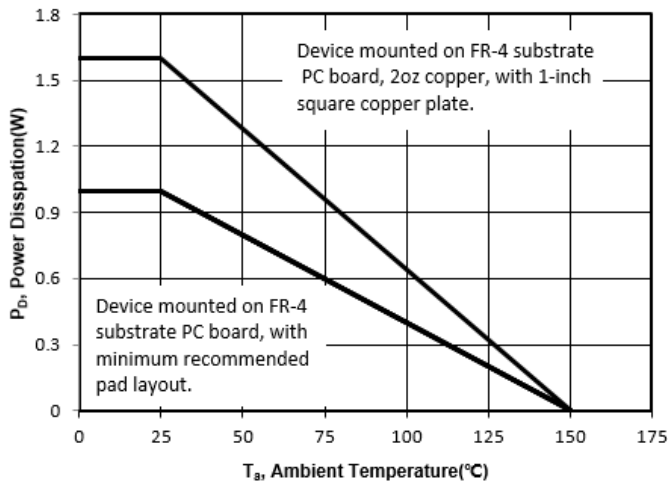


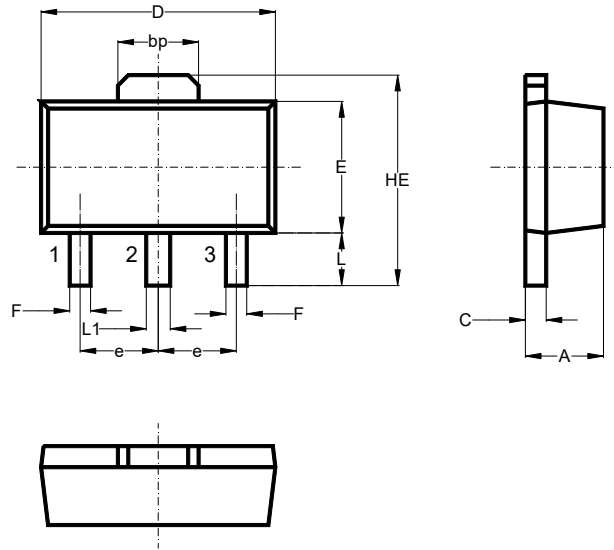
Fig 7. Power Derating Curve



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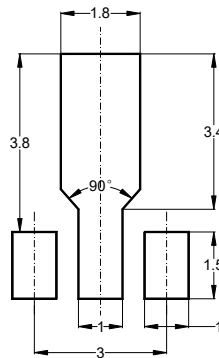
Package Outline (Dimensions in mm)

SOT-89



Unit	A	bp	C	D	E	F	HE	e	L	L1
mm	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-89	12	8 ± 0.1	0.315 ± 0.004	178	7	1,000
				330	13	4,000

Marking information

" 2SD350U " = Part No.
 "YM" = Date Code Marking
 "Y" = Year
 "M" = Month
 Font type: Arial

